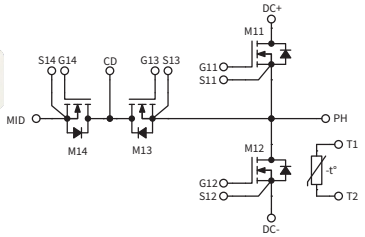
CHB011M12GM4, CHB011M12GM4T

V_{DS}	1200 V
$R_{DS(on)}$	11 mΩ

1200 V, 11 mΩ, Silicon Carbide, T-Type Module



Technical Features

- Ultra-Low Loss
- High Frequency Operation
- Zero Turn-Off Tail Current from MOSFET
- Normally-Off, Fail-Safe Device Operation
- Optional Pre-Applied Thermal Interface Material
- Features Gen4 Technology with Soft Body Diode

Typical Applications

- EV Chargers
- High-Efficiency Converters / Inverters
- Renewable Energy
- Smart-Grid / Grid-Tied Distributed Generation

System Benefits

- Enables Compact, Lightweight Systems
- Increased System Efficiency, due to Low Switching & Conduction Losses of SiC
- Reduced Thermal Requirements and System Cost

Key Parameters

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Note
Drain-Source Voltage	V_{DS}			1200	V	T_{HS} = 25 °C	
Maximum Gate-Source Voltage	$V_{GS(max)}$	-8		+19		Transient	Fig. 32 Note 1
Operational Gate-Source Voltage	$V_{GS(op)}$		-4/15			Static	
DC Continuous Drain Current (T_{VJ} ≤ 150 °C)	I_D			100	A	V_{GS} = 15 V, T_{HS} = 50 °C, T_{VJ} ≤ 150 °C	Notes 2,3 Fig. 20
DC Continuous Drain Current (T_{VJ} ≤ 175 °C)				100		V_{GS} = 15 V, T_{HS} = 50 °C, T_{VJ} ≤ 175 °C	
Pulsed Drain Current	I_{DM}			200		t_{Pmax} limited by T_{VJmax} V_{GS} = 15 V, T_{HS} = 50 °C	
Power Dissipation	P_D		265		W	T_{HS} = 50 °C, T_{VJ} ≤ 175 °C	Note 4 Fig. 20
Virtual Junction Temperature	$T_{VJ(op)}$	-40		150	°C	Operation	
		-40		175	°C	Intermittent with Reduced Life	

Note (1): Recommended turn-on gate voltage is 15 V with ±5% regulation tolerance
Note (2): Current limit at T_{HS} = 50°C calculated by $I_{D(max)} = \sqrt{(P_D / R_{DS(typ)}(T_{VJ(max)}, I_{D(max)})}$
Note (3): Verified by design
Note (4): $P_D = (T_{VJ} - T_{HS})/R_{TH(JH,typ)}$

MOSFET Characteristics (Per Position) (T_{VJ} = 25 °C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Note
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200			V	V_{GS} = 0 V, T_{VJ} = -40 °C	
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.5	4.0		V_{DS} = V_{GS}, I_D = 28 mA	
			2.0			V_{DS} = V_{GS}, I_D = 28 mA, T_{VJ} = 175°C	
Zero Gate Voltage Drain Current	I_{DSS}		3	300	µA	V_{GS} = 0 V, V_{DS} = 1200 V	
Gate-Source Leakage Current	I_{GSS}		60	1200	nA	V_{GS} = 19 V, V_{DS} = 0 V	
Drain-Source On-State Resistance (Devices Only)	$R_{DS(on)}$		11.0	14.9	mΩ	V_{GS} = 15 V, I_D = 100 A	Fig. 2 Fig. 3
			17.6			V_{GS} = 15 V, I_D = 100 A, T_{VJ} = 150 °C	
			19.8			V_{GS} = 15 V, I_D = 100 A, T_{VJ} = 175 °C	
Transconductance	g_{fs}		77		S	V_{DS} = 20 V, I_D = 100 A	Fig. 4
			78			V_{DS} = 20 V, I_D = 100 A, T_{VJ} = 175 °C	
Turn-On Switching Energy, T_{VJ} = 25 °C T_{VJ} = 125 °C T_{VJ} = 175 °C	E_{On}		0.29 0.26 0.25		mJ	V_{DD} = 400 V, I_D = 100 A, V_{GS} = -4 V/15 V, $R_{G(OFF)}$ = 0 Ω, $R_{G(ON)}$ = 0 Ω, L_σ = 25 nH	Fig. 11 Fig. 13
Turn-Off Switching Energy, T_{VJ} = 25 °C T_{VJ} = 125 °C T_{VJ} = 175 °C	E_{Off}		0.13 0.11 0.12				
Internal Gate Resistance	$R_{G(int)}$		1.4		Ω	f = 100 kHz	
Input Capacitance	C_{iss}		10.1		nF	V_{GS} = 0 V, V_{DS} = 800 V, V_{AC} = 25 mV, f = 100 kHz	Fig. 9
Output Capacitance	C_{oss}		0.4				
Reverse Transfer Capacitance	C_{rss}		36		pF		
Gate to Source Charge	Q_{GS}		180		nC	V_{DS} = 800 V, V_{GS} = -4 V/15 V, I_D = 100 A, Per IEC60747-8-4 pg 21	
Gate to Drain Charge	Q_{GD}		96				
Total Gate Charge	Q_G		405				
FET Thermal Resistance, Junction to Heatsink	$R_{th\ JH}$		0.472		°C/W	Measured with Pre-Applied TIM	Fig. 17

Diode Characteristics (Per Position) (T_{VJ} = 25 °C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Notes
Body Diode Forward Voltage	V_{SD}		5.8		V	V_{GS} = -4 V, I_{SD} = 100 A	Fig. 7
			5.4			V_{GS} = -4 V, I_{SD} = 100 A, T_{VJ} = 175 °C	
DC Source-Drain Current (Body Diode)	$I_{SD\ BD}$		58		A	V_{GS} = -4 V, T_{HS} = 50 °C, T_{VJ} ≤ 175 °C	Notes 2,3 Fig. 20
Reverse Recovery Time	t_{RR}		27.0		ns	V_{GS} = -4 V, I_{SD} = 100 A, V_R = 400 V di/dt = 12.8 A/ns, T_{VJ} = 175 °C	Fig. 31
Reverse Recovery Charge	Q_{RR}		2.2		µC		
Peak Reverse Recovery Current	I_{RRM}		149		A		
Reverse Recovery Energy, T_{VJ} = 25 °C T_{VJ} = 125 °C T_{VJ} = 175 °C	E_{RR}		0.53 0.54 0.73		mJ	V_{DD} = 400 V, I_D = 100 A, V_{GS} = -4 V/15 V, $R_{G(ON)}$ = 0 Ω, L_σ = 25 nH	Fig. 14

Module Physical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Package Resistance, M11	R_{pkg1}		0.57		mΩ	T_{HS} = 125°C, Note 5
Package Resistance, M12	R_{pkg2}		0.76			
Package Resistance, M13 & M14	R_{pkg3}		0.81			
Stray Inductance	L_{Stray1}		17.5		nH	Between MID and DC+, f = 10 MHz
	L_{Stray2}		23.8			Between MID and DC-, f = 10 MHz
Case Temperature	T_C	-40		125	°C	
Mounting Torque	M_S		2.0	2.3	N-m	M4 bolts
Weight	W		39		g	
Case Isolation Voltage	V_{isol}	3			kV	AC, 50 Hz, 1 minute
Comparative Tracking Index	CTI	200				
Clearance Distance			5.0		mm	Terminal to Terminal
			10.0			Terminal to Heatsink
Creepage Distance			6.3			Terminal to Terminal
			11.5			Terminal to Heatsink

Note (5): Total Effective Resistance (Per Switch Position) = MOSFET $R_{DS(on)}$ + Switch Position Package Resistance

NTC Thermistor Characterization

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rated Resistance	R_{NTC}		5.0		kΩ	T_{NTC} = 25°C
Resistance Tolerance at 25 °C	ΔR/R	-5		5	%	
Beta Value (T_2 = 50 °C)	$ß_{25/50}$		3380		K	
Beta Value (T_2 = 80 °C)	$ß_{25/80}$		3468		K	
Beta Value (T_2 = 100 °C)	$ß_{25/100}$		3523		K	
Power Dissipation	P_{Max}			10	mW	T_{NTC} = 25°C

Typical Performance

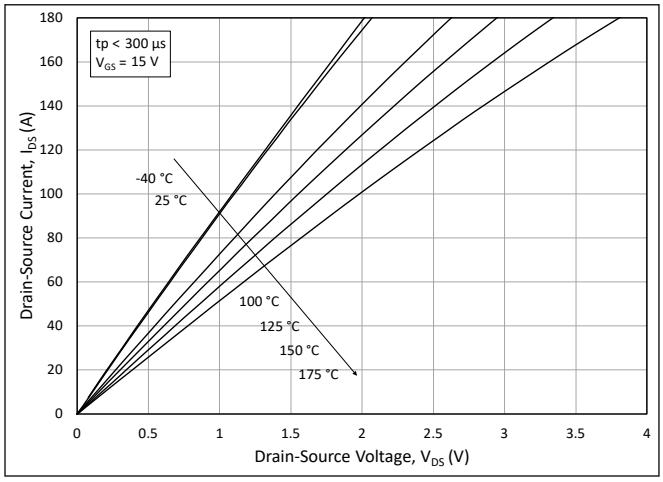


Figure 1. Output Characteristics for Various Junction Temperatures

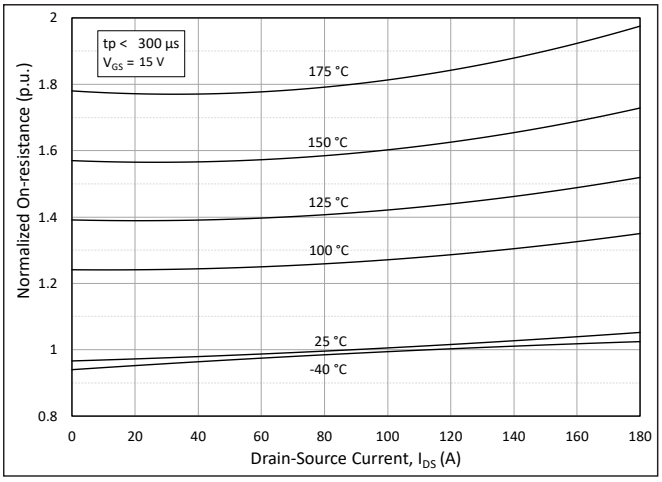


Figure 2. Normalized On-State Resistance vs. Drain Current for Various Junction Temperatures

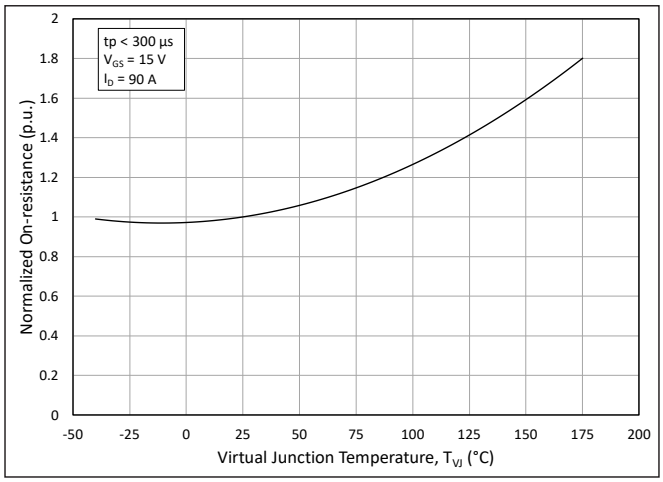


Figure 3. Normalized On-State Resistance vs. Junction Temperature

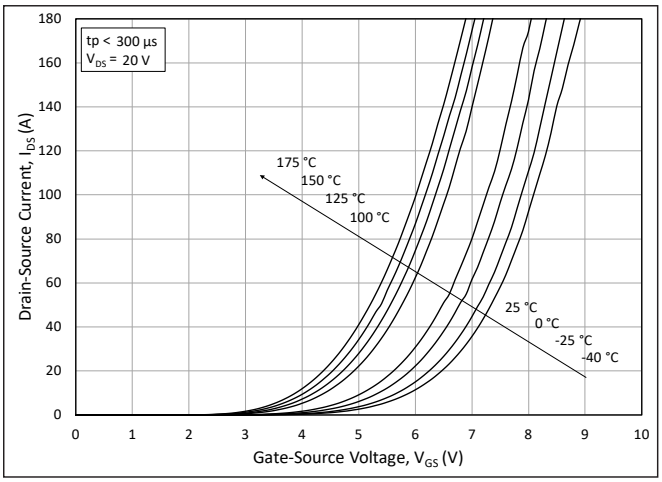


Figure 4. Transfer Characteristic for Various Junction Temperatures

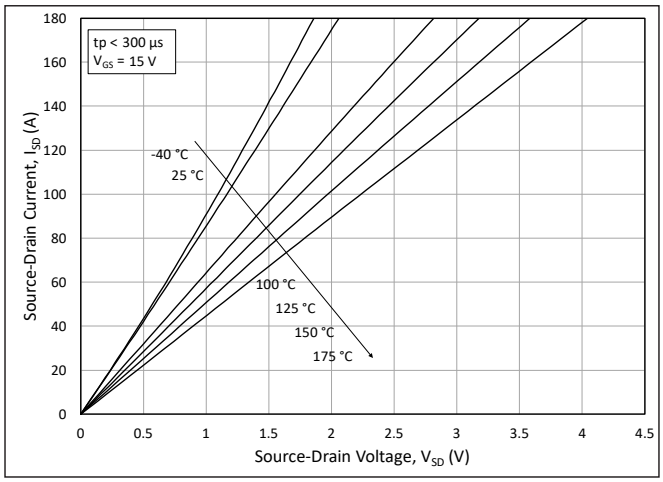


Figure 5. 3rd Quadrant Characteristic vs. Junction Temperatures at V_{GS} = 15 V

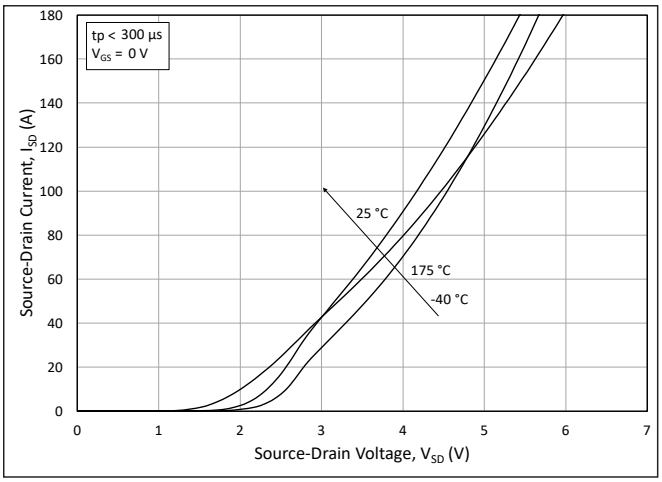


Figure 6. 3rd Quadrant Characteristic vs. Junction Temperatures at V_{GS} = 0 V (Body Diode)

Typical Performance

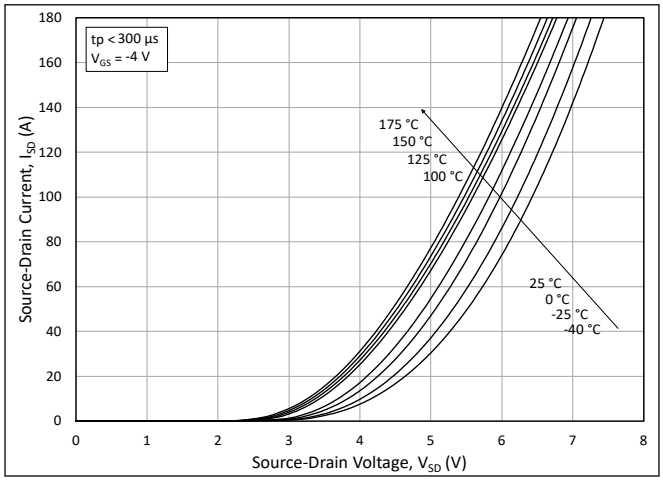


Figure 7. 3rd Quadrant Characteristic vs. Junction Temperatures at V_{GS} = - 4 V (Body Diode)

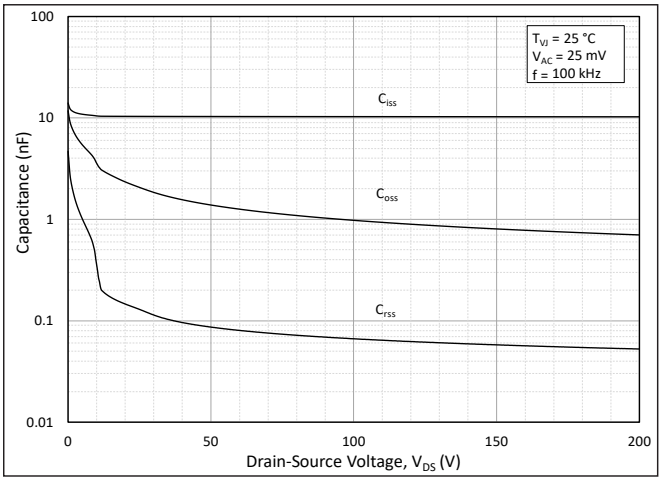


Figure 8. Typical Capacitances vs. Drain to Source Voltage (0 - 200V)

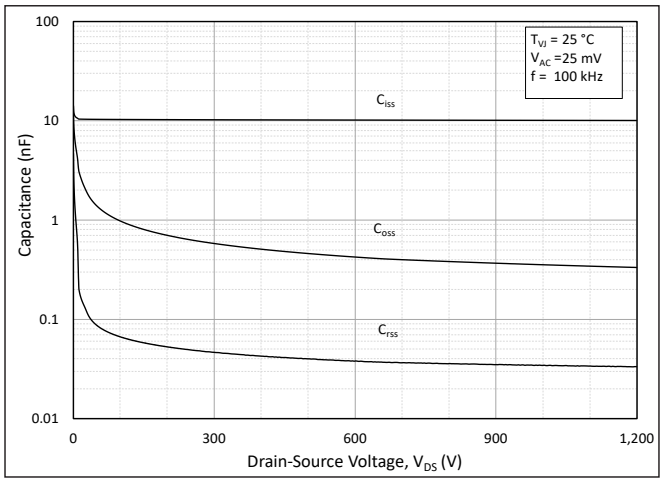


Figure 9. Typical Capacitances vs. Drain to Source Voltage (0 - 1200V)

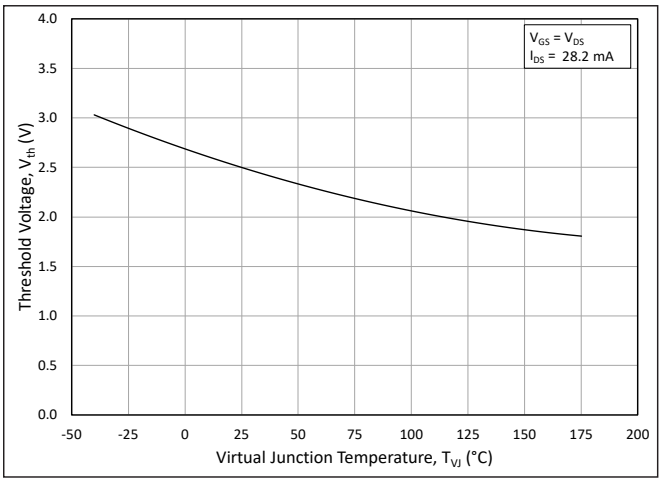


Figure 10. Threshold Voltage vs. Junction Temperature

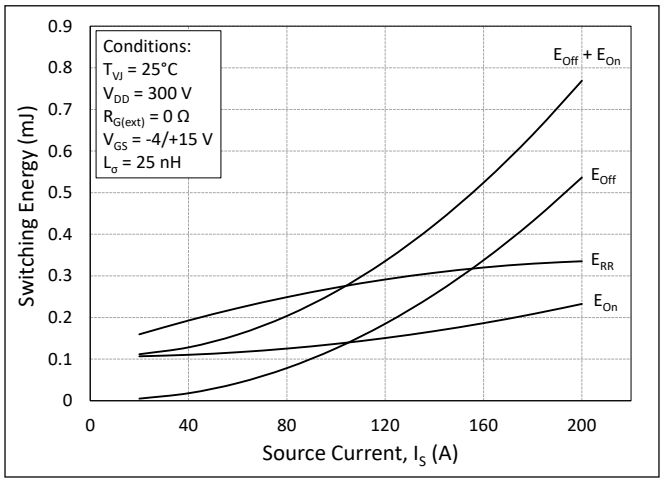


Figure 11. Switching Energy vs. Drain Current (V_{DD} = 300 V)

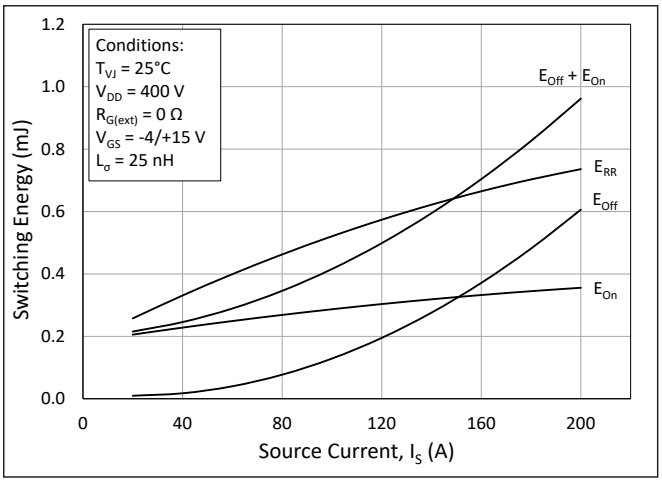


Figure 12. Switching Energy vs. Drain Current (V_{DD} = 400 V)

Typical Performance

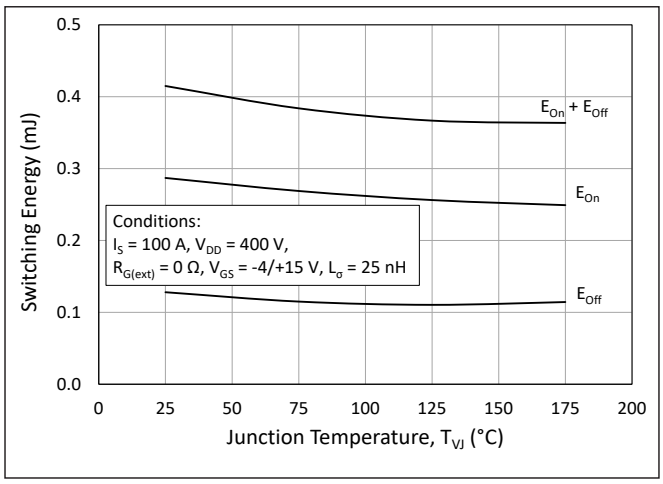


Figure 13. MOSFET Switching Energy vs. Junction Temperature

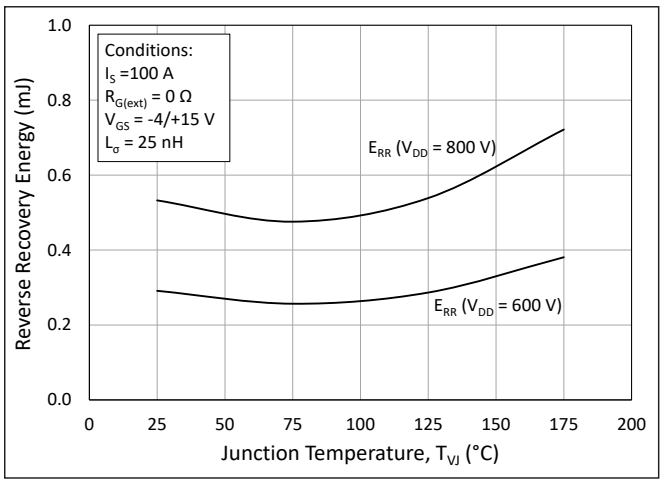


Figure 14. Reverse Recovery Energy vs. Junction Temperature

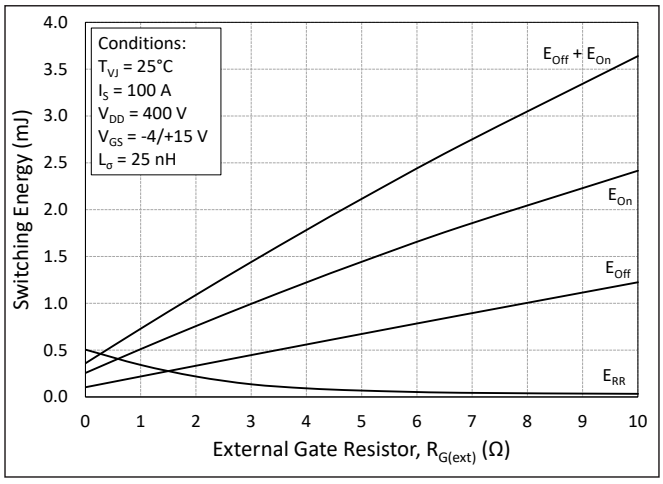


Figure 15. MOSFET Switching Energy vs. External Gate Resistance

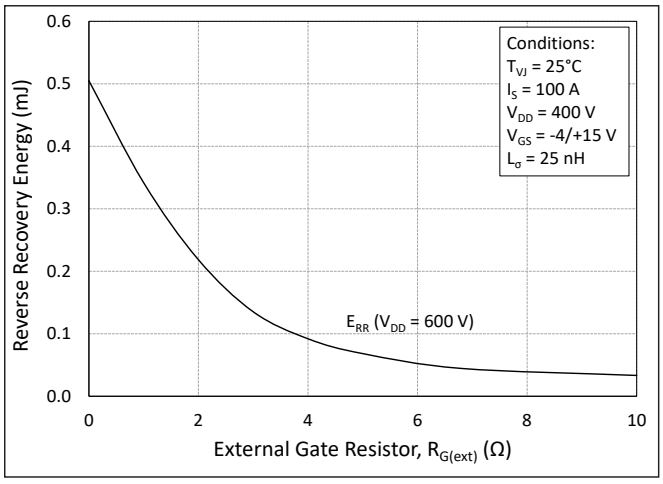


Figure 16. Reverse Recovery Energy vs. External Gate Resistance

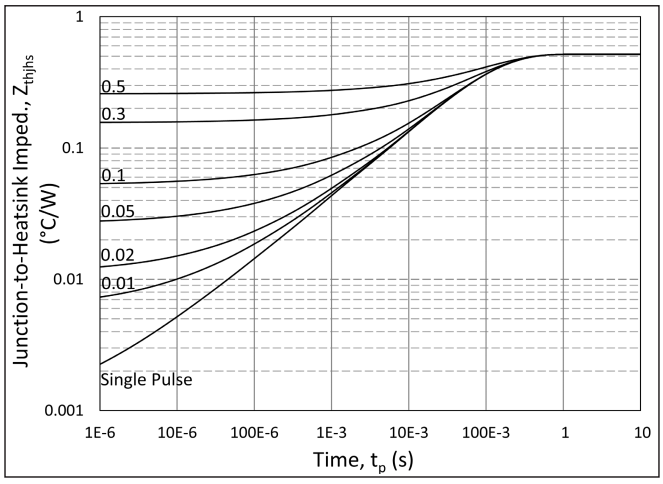


Figure 17. MOSFET Junction to Heastsink Transient Thermal Impedance, $Z_{th\ JHS}$ (°C/W)

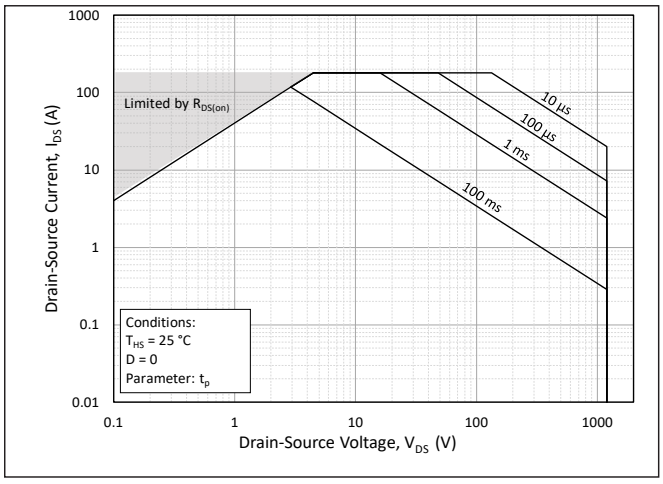


Figure 18. Forward Bias Safe Operating Area (FBSOA)

Typical Performance

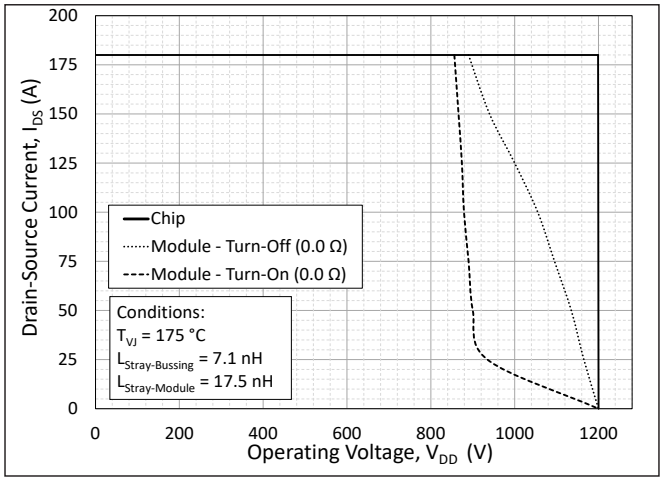


Figure 19. Switching Safe Operating Area

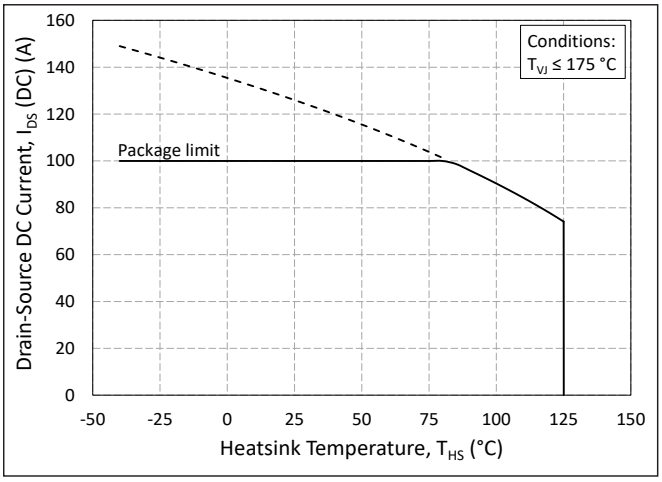


Figure 20. Continuous Drain Current Derating vs. Case Temperature

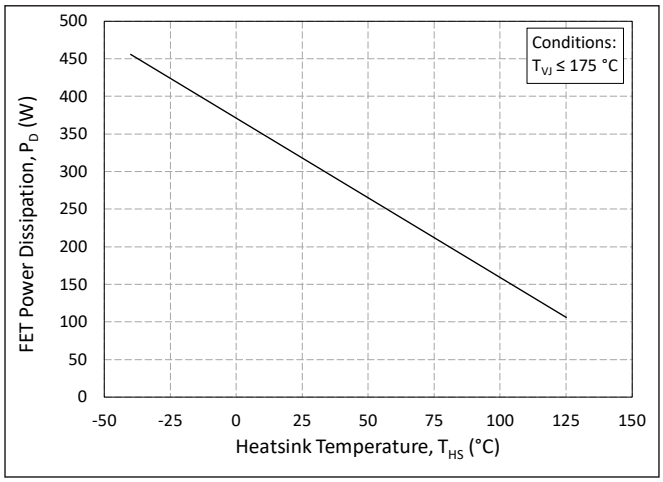


Figure 21. Maximum Power Dissipation Derating vs. Case Temperature

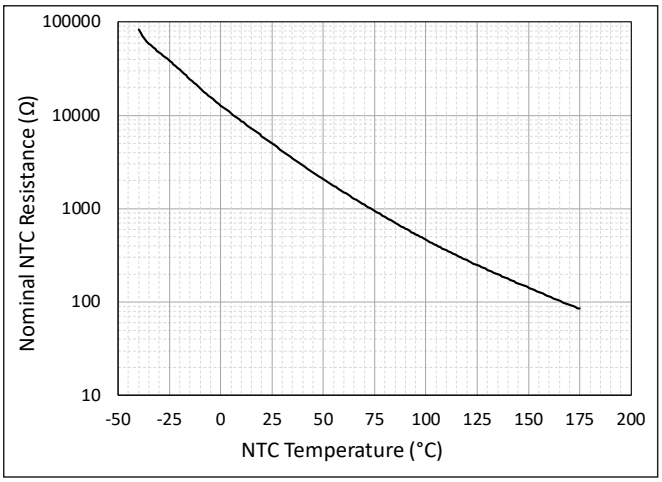


Figure 22. Nominal NTC Resistance vs. NTC Temperature

Note (6): Figures 1-10 are representative of the static MOSFET characteristics for all four switch positions.
Note (7): Figures 11-28 are representative of switch positions M11 and M14 (page 10) corresponding to the top-side high-frequency loop. The circuits for switching loss and reverse recovery measurements are shown in figures 33 and 34.
Note (8): The CGD1700HB2M-UNA, which features the UCC21710 gate driver IC from Texas Instruments, was used to evaluate dynamic performance. The typical parasitic turn-on resistance of 2.5 Ω and the parasitic turn-off resistance of 0.3 Ω are not included in the $R_{G(ext)}$ values on this datasheet.

Timing Characteristics

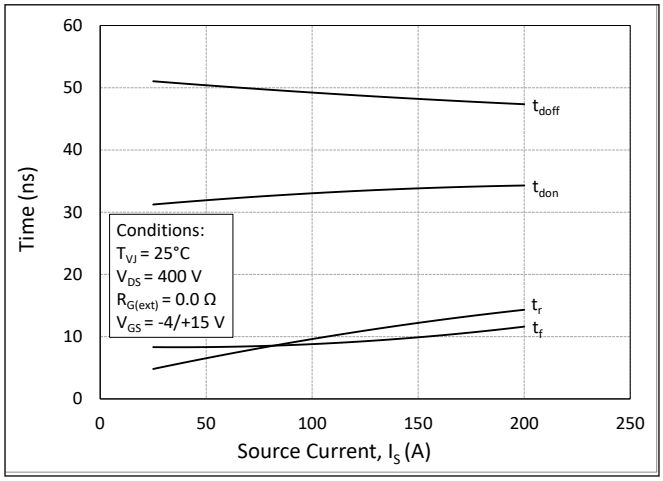


Figure 23. Timing vs. Source Current

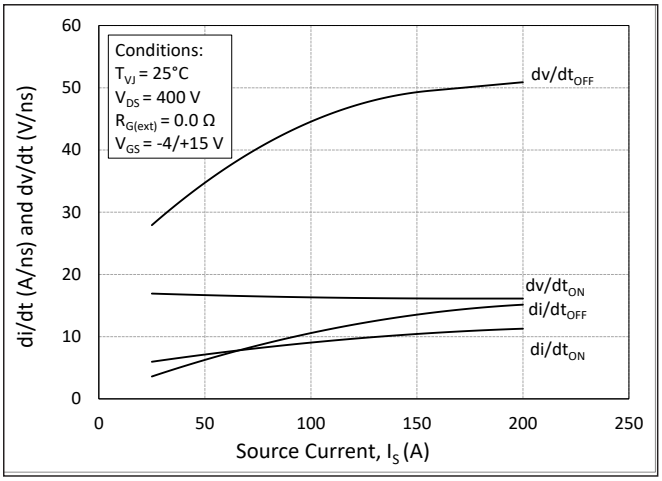


Figure 24. dv/dt and di/dt vs. Source Current

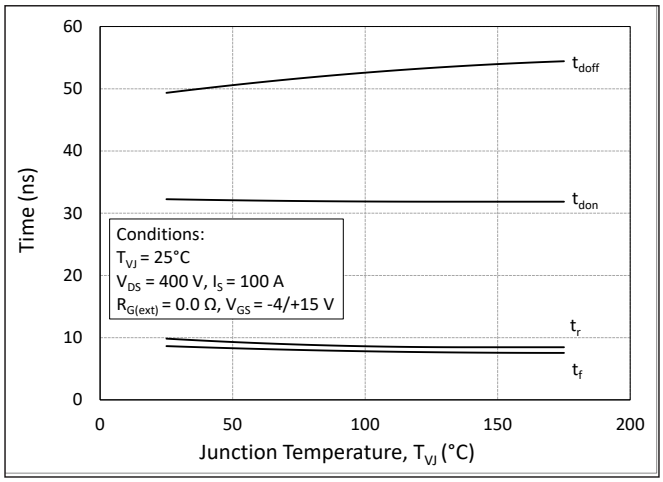


Figure 25. Timing vs. Junction Temperature

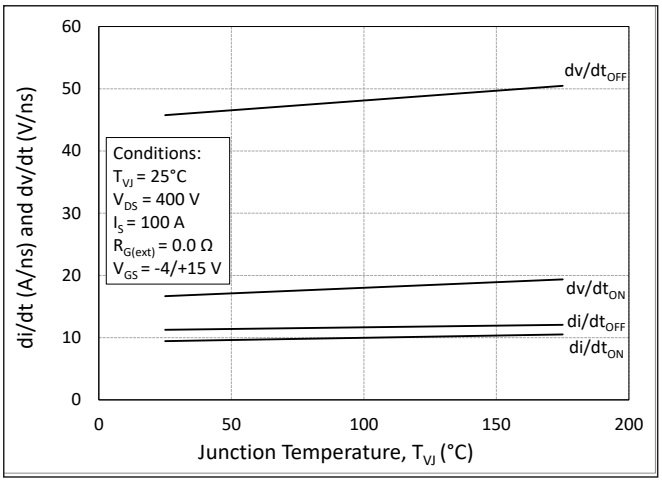


Figure 26. dv/dt and di/dt vs. Junction Temperature

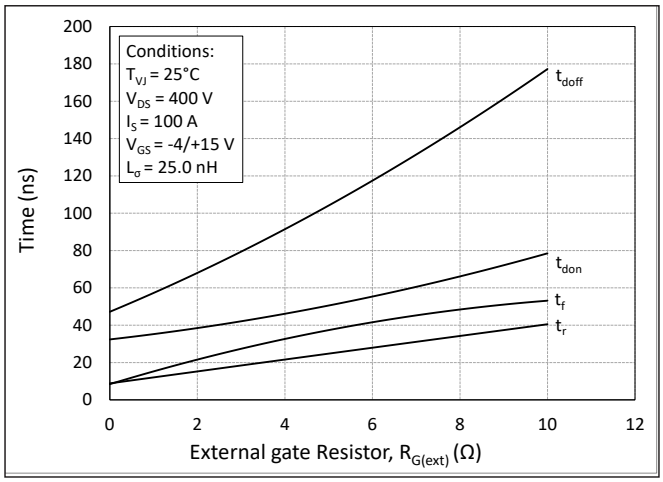


Figure 27. Timing vs. External Gate Resistance

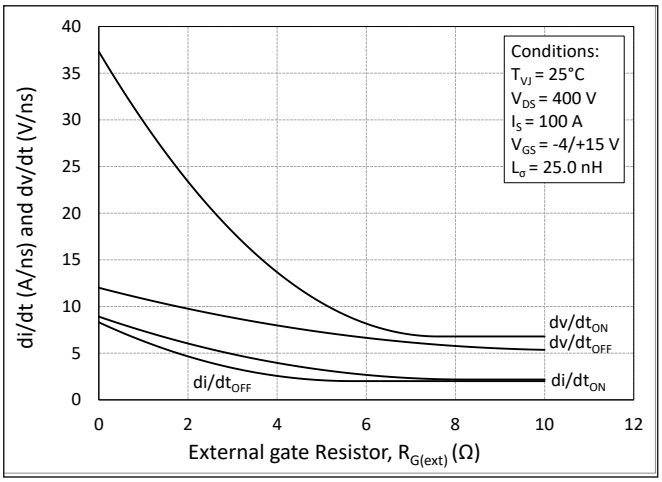


Figure 28. dv/dt and di/dt vs. External Gate Resistance

Definitions

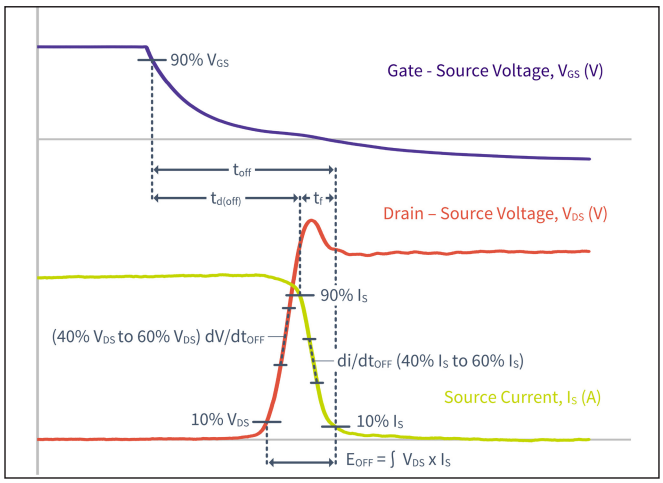


Figure 29. Turn-off Transient Definitions

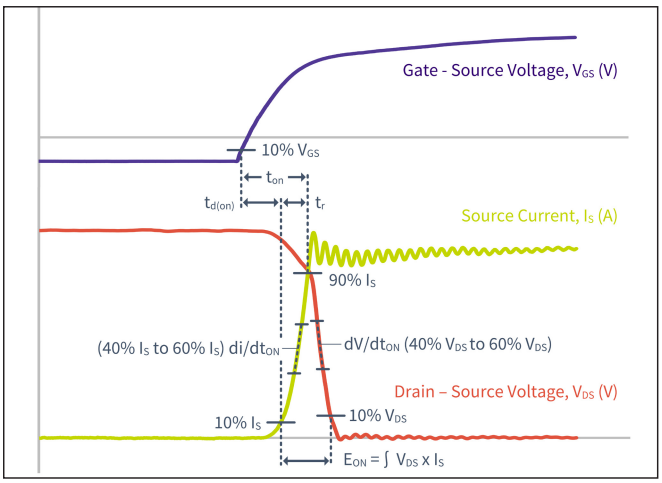


Figure 30. Turn-on Transient Definitions

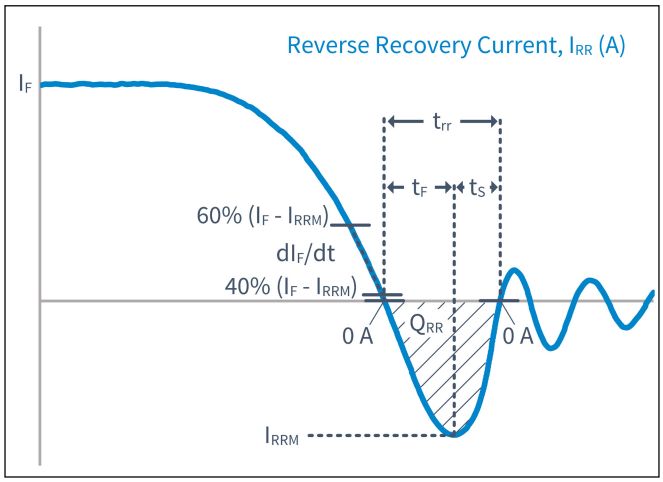


Figure 31. Reverse Recovery Definitions

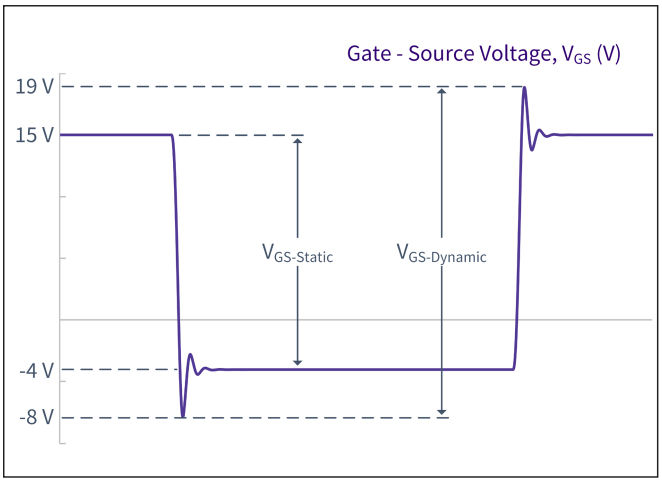


Figure 32. V_{GS} Transient Definitions

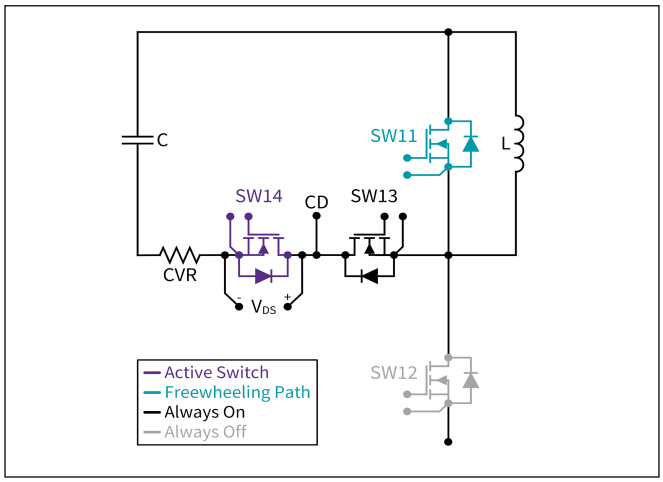


Figure 33. Switching Loss Measurement

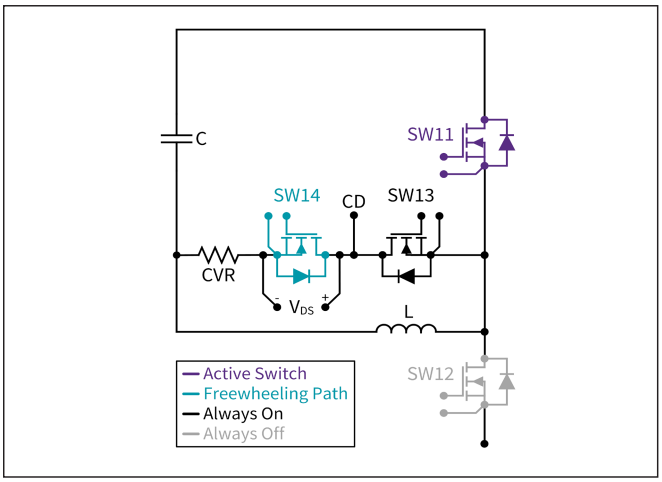
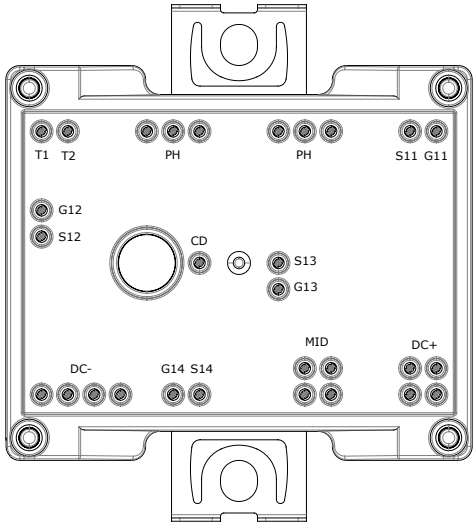
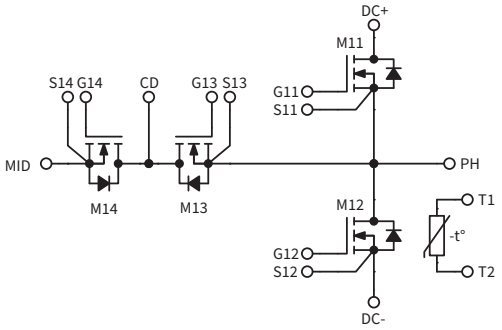


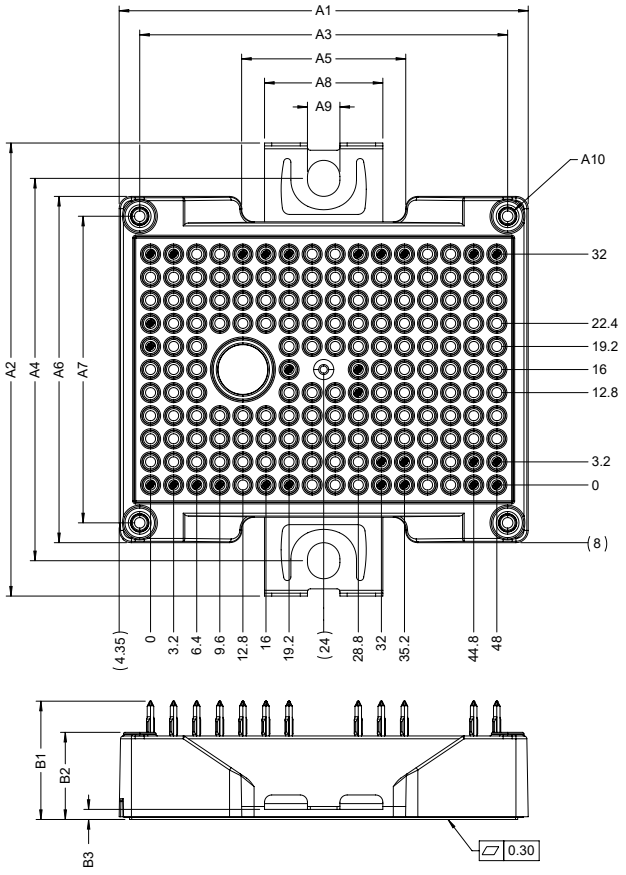
Figure 34. Reverse Recovery Measurement

Schematic and Pin Out





Package Dimension (mm)



DIMENSION TABLE		
SYMBOL	DIMENSION	TOLERANCE
A1	56.7	±0.30
A2	62.8	±0.50
A3	51	±0.15
A4	(53)	REF.
A5	22.7	±0.30
A6	48	±0.30
A7	42.5	±0.15
A8	16.4	±0.20
A9	4.5	±0.10
A10	⌀2.3 ↧8.5	⌀: +0 -0.10 ↧: ±0.30
B1	16.4	±0.50
B2	12.0	±0.35
B3	1.4	±0.20
ALL PIN LOCATIONS		±0.40

Product Ordering Code

Part Number	Description
CHB011M12GM4	Without Pre-Applied Phase Change Thermal Interface Material
CHB011M12GM4T	With Pre-Applied Phase Change Thermal Interface Material

Supporting Links & Tools

Evaluation Tools & Support

- All LTSpice Models
- All PLECS Models
- SpeedFit 2.0 Design Simulator™
- Technical Support Forum

Dual-Channel Gate Driver Board

- EVAL-ADUM4146WHB1Z: Analog Devices® Gate Driver Board
- Si823H-AxWA-KIT: Skyworks® Gate Driver Board
- ACPL-355JC: Broadcom® Gate Driver Board
- CGD1700HB2M-UNA: Wolfspeed Gate Driver Board
- CGD12HB00D: Differential Transceiver Daughter Board Companion Tool for Differential Gate Drivers

Application Notes

- CPWR-AN41: Mounting Instructions and PCB Requirements
- CPWR-AN42: Thermal Interface Material Application Note
- CPWR-AN45: Dynamic Performance Application Note

Notes & Disclaimers

WOLFSPEED PROVIDES TECHNICAL AND RELIABILITY DATA, DESIGN RESOURCES, APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, WITH RESPECT THERETO, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, SUITABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD-PARTY INTELLECTUAL PROPERTY RIGHTS.

This document and the information contained herein are subject to change without notice. Any such change shall be evidenced by the publication of an updated version of this document by Wolfspeed. No communication from any employee or agent of Wolfspeed or any third party shall effect an amendment or modification of this document. No responsibility is assumed by Wolfspeed for any infringement of patents or other rights of third parties which may result from use of the information contained herein. No license is granted by implication or otherwise under any patent or patent rights of Wolfspeed.

The information contained in this document (excluding examples, as well as figures or values that are labeled as "typical") constitutes Wolfspeed's sole published specifications for the subject product. "Typical" parameters are the average values expected by Wolfspeed in large quantities and are provided for informational purposes only. Any examples provided herein have not been produced under conditions intended to replicate any specific end use. Product performance can and does vary due to a number of factors.

This product has not been designed or tested for use in, and is not intended for use in, any application in which failure of the product would reasonably be expected to cause death, personal injury, or property damage. For purposes of (but without limiting) the foregoing, this product is not designed, intended, or authorized for use as a critical component in equipment implanted into the human body, life-support machines, cardiac defibrillators, and similar emergency medical equipment; air traffic control systems; or equipment used in the planning, construction, maintenance, or operation of nuclear facilities. Notwithstanding any application-specific information, guidance, assistance, or support that Wolfspeed may provide, the buyer of this product is solely responsible for determining the suitability of this product for the buyer's purposes, including without limitation (1) selecting the appropriate Wolfspeed products for the buyer's application, (2) designing, validating, and testing the buyer's application, and (3) ensuring the buyer's application meets applicable standards and any other legal, regulatory, and safety-related requirements.

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfspeed representative or from the Product Documentation sections of www.wolfspeed.com.

REACh Compliance

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact your Wolfspeed representative to ensure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

Contact info:
4600 Silicon Drive
Durham, NC 27703 USA
Tel: +1.919.313.5300
www.wolfspeed.com/power

© 2024 Wolfspeed, Inc. All rights reserved. Wolfspeed® and the Wolfstreak logo are registered trademarks and the Wolfspeed logo is a trademark of Wolfspeed, Inc.
The information in this document is subject to change without notice.